Amendments to the Specification:

Please replace the paragraph beginning at page 7, line 12 as with the following amended paragraph:

It should be noted that, in the plasma generating step, the raw gas may be supplied simultaneously when the output of the RF power supply becomes identical with the value which is **[[9]]** at the time of forming the film. Alternatively, the raw gas may be supplied while shifting a timing at which the output of the RF power supply becomes identical with the value which is at the time of forming the film. Further, the lower limit of the RF output when oscillation starts can be defined by a dischargeable value.

Please replace the paragraph beginning at page 11, line 1 as with the following amended paragraph:

Then, an aluminum film with a thickness of 6000 Å that constitutes a gate electrode 105 is deposited through sputtering. The aluminum film contains scandium of 0.1 to 0.3 weight % therein. Then, an anodization (aluminum oxide) **[[film]]** layer 106 is formed on the surface of the aluminum film through anodization. In this situation, a voltage of 10 to 30 V is applied to the aluminum film in an ethylene glycol solution containing tartaric acid of 3% therein. The anodization layer 106 thus formed has a fine (barrier-type) structure. Then, a resist mask **[[106]]** 107 is formed on the surface of the anodization layer 106, and the aluminum film is patterned to form a gate electrode **[[107]]** 105 (Fig. 1A).

Please replace the paragraph beginning at page 11, line 11 as with the following amended paragraph:

As shown in Fig. lB, a constant voltage of 10 to 30 V applied to the gate electrode 105 in the electrolyte solution while the resist mask **[[106]]** 107 is attached to the anodization layer, to thereby conduct anodization. As the electrolyte solution, there can be used an acid solution in which citric acid, oxalic acid or sulfuric acid is diluted to 3 to 20%. In this embodiment, a voltage of 10 V is applied to the gate electrode 107 in oxalic acid solution (30 °C) for 20 to 40

minutes. As a result, a porous type anodic oxide 108 with a thickness of 5000 Å is formed on only sides of the gate electrode 105. It should be noted that the thickness of the oxidation 108 may be controlled by oxidation time (Fig. 1B).

Please replace the paragraph beginning at page 13, line 9 as with the following amended paragraph:

Subsequently, a silicon oxide film 116 with a thickness of 5000 Å is deposited as an interlayer insulator with a raw material of TEOS through plasma CVD. In this embodiment, in order that the beard pulse as shown in Fig. 6C is eliminated or suppressed between the RF electrodes in the initial stage of forming a film, the output of the RF power supply in a plasma CVD device is gradually increased. For that reason, the RF output is first set to 50 W to generate O_2 plasma. Thereafter, simultaneously when the RF output is increased to 250 W, TEOS gas is supplied to generate TEOS/O_2 plasma, thereby forming a silicon oxide film **[[110]]** 116.